## SKN 400

	V <sub>RSM</sub>	V <sub>RRM</sub>	I <sub>FRMS</sub> = 700 A (ma	ximum value for continuous oper	ation)
	V	V	I <sub>FAV</sub> = 4	I <sub>FAV</sub> = 400 A (sin. 180; T <sub>c</sub> = 100 °C)	
	1800	1800	SKN 400/18		
	2400	2400	SKN 400/24		
	2700	2700	SKN 400/27		
	3000	3000	SKN 400/30		
	Symbol Conditions		Values	Units	
	I <sub>FAV</sub>	sin. 180; T <sub>c</sub> = 85 (100) °C		445 (400)	А
	ID	K 0,55; T <sub>a</sub> = 45 °C; B2 / B6		310 / 450	A
Stud Diode		K 0,55F; T <sub>a</sub> = 35 °C	; B2 / B6	700 / 1000	А
Rectifier Diode	I <sub>FSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms T <sub>vi</sub> = 160 °C; 10 ms		9000	Α
				7500	А
	i²t	T <sub>vi</sub> = 25 °C; 8,3 10 ms		400000	A²s
	T <sub>vi</sub> = 160 °C; 8,3 10 ms		280000	A²s	
	V <sub>F</sub>	T <sub>vi</sub> = 25 °C; I <sub>F</sub> = 1200 A		max. 1,45	V
SKN 400	V <sub>(TO)</sub>	$T_{v_i}^{i} = 160 \ ^{\circ}C$		max. 0,9	V
	r <sub>T</sub>	T <sub>vi</sub> = 160 °C		max. 0,5	mΩ
	$I_{RD}$ $T_{vj} = 160 \text{ °C}; V_{RD} = V_{RRM}$		max. 60	mA	
	Q <sub>rr</sub>	T <sub>vj</sub> = 160 °C; - di <sub>F</sub> /dt = 10 A/μs		400	μC
	R <sub>th(j-c)</sub>			0,11	K/W
	R <sub>th(c-s)</sub>			0,01	K/W
	T <sub>vi</sub>			- 40 + 160	°C
Features	T <sub>stg</sub>			- 55 + 160	°C
Reverse voltages up to 3000 V	V <sub>isol</sub>			-	٧~
Hermetic metal case with ceramic	M <sub>s</sub> to heatsink		60	Nm	
insulator with extra long creepage	a			5 * 9,81	m/s²
distances	m	approx.		500	g
Threaded stud ISO M24 x 1,5	Case			E 17	-
SKN: anode to stud					

## **Typical Applications**

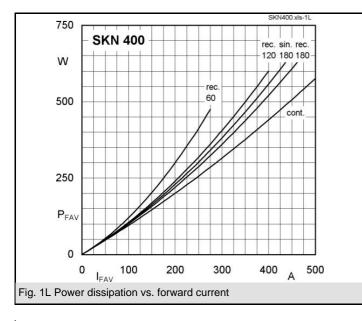
- High voltage rectifier diode, especially for traction applications
- Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes

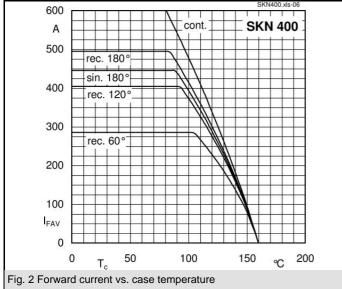
SKN

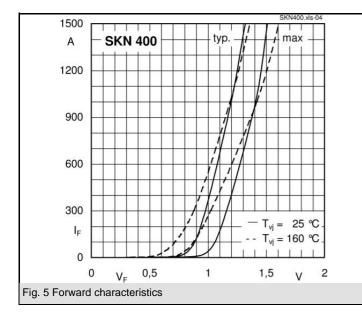
• Recommended snubber network: RC: 1  $\mu$ F, 20  $\Omega$  (P<sub>R</sub> = 2 W), R<sub>p</sub> = 25 k $\Omega$  (P<sub>R</sub> = 20 W)

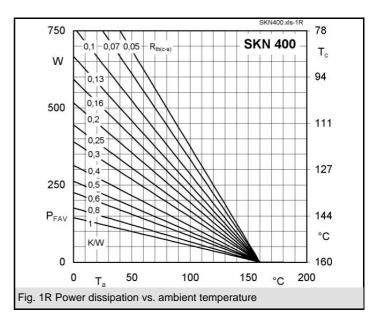


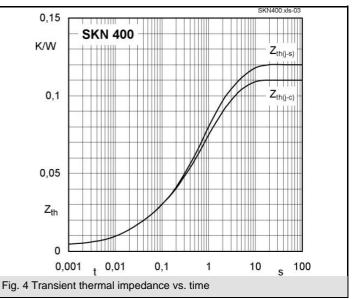
## **SKN 400**

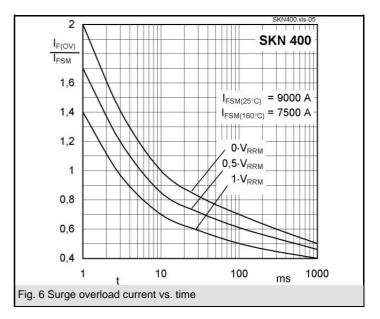




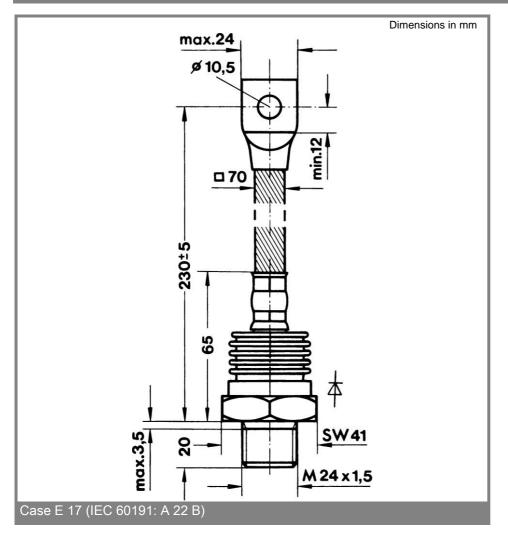








## SKN 400



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